

AS6C1616-55BIN , AS6C1616A-55BIN & AS6C1616B-55BIN

Comparison

Part Number & result Parameter	AS6C1616-55BIN	AS6C1616A-55BIN	AS6C1616B-55BIN	Comments
ProductDescription	Low Power ASRAM	Low Power ASRAM rev.A	Low Power ASRAM rev.B	
Capacity	16Mb	16Mb	16Mb	Same
Memory Organization	1024K x 16bits	1024K x 16bits	1024K x 16bits	Same
Oper. Power Supply	V _{CC} =2.7V ~ 3.6V	V _{CC} =2.7V ~ 3.6V	V _{CC} =2.7V ~ 3.6V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	CIO: 8pf (Max.)	CIO: 10pf (Max.)	CIO: 8pf (Max.)	Diff
Read Cycle Time (tRC)	55ns (Min.)	55ns (Min.)	55ns (Min.)	Same
Write Cycle Time (tWC)	55ns (Min.)	55ns (Min.)	55ns (Min.)	Same
AddrAccessTime(tAA)	55ns (Max.)	55ns (Max.)	55ns (Max.)	Same
OE Access Time (tOE)	30ns (Max.)	35ns (Max.)	30ns (Max.)	Diff
V_{OH}(V) @ -1.0mA	2.2 (Min.)	2.4 (Min.)	2.2 (Min.)	Diff
V_{OL} (V) @ 2mA	0.4 (Max.)	0.4 (Max.)	0.4 (Max.)	Same
V_{IH} (V)	2.2 (Min.)	2.2 (Min.)	2.2 (Min.)	Same
V_{IL} (V)	0.6 (Max.)	0.6 (Max.)	0.6 (Max.)	Same
I_{LI} / I_{LO}(uA)	1 (Max.)	1 (Max.)	1 (Max.)	Same
Oper. Current (Cycle Time=55ns)	I _{CC} = 60mA	I _{CC2} = 70mA	I _{CC} = 18mA	Diff
Oper. Current (Cycle Time=1us)	I _{CC1} = 16mA (Max.)	I _{CC1} = 8mA (Max.)	I _{CC1} = 5mA (Max.)	Diff
StandbyCurrent I_{SB1}	40uA (Max.)	30uA (Max.)	40uA (Max.)	Diff
V_{DR}	1.2 (Min.)	1.5V (Min.)	1.5V (Min.)	Diff
Package TFBGA Outer Dimensions	6mm x 8mm	8mm x 10mm	6mm x 8mm	Diff
Ball pitch and array	0.75mm, 3.75 x 5.25mm	0.75mm, 3.75 x 5.25mm	0.75mm, 3.75 x 5.25mm	same
Package Material	Pb and Halogen Free			Same
Pin to Pin Compatible	Yes	Yes	Yes	Same